Complementary NPN-PNP Power Bipolar Transistors

These complementary devices are lower power versions of the popular NJW3281G and NJW1302G audio output transistors. With superior gain linearity and safe operating area performance, these transistors are ideal for high fidelity audio amplifier output stages and other linear applications.

Features

- Exceptional Safe Operating Area
- NPN/PNP Gain Matching within 10% from 50 mA to 3 A
- Excellent Gain Linearity
- High BVCEO
- High Frequency
- These Devices are Pb-Free and are RoHS Compliant

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

Applications

- High-End Consumer Audio Products
 - Home Amplifiers
 - Home Receivers
- Professional Audio Amplifiers
 - Theater and Stadium Sound Systems
 - Public Address Systems (PAs)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	250	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	250	Vdc
Collector Current - Continuous	I _C	15	Adc
Collector Current - Peak (Note 1)	I _{CM}	30	Adc
Base Current - Continuous	Ι _Β	1.5	Adc
Total Power Dissipation @ T _C = 25°C	P_{D}	150	Watts
Operating and Storage Junction Temperature Range	T _J , T _{stg}	- 65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

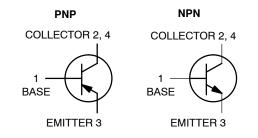
1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.

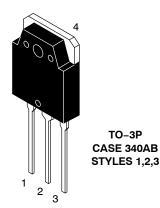


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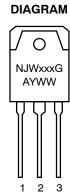
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15 AMPERES **COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 150 WATTS**





TO-3P



MARKING

= 0281 or 0302 XXXX G = Pb-Free Package = Assembly Location = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NJW0281G	TO-3P (Pb-Free)	30 Units/Rail
NJW0302G	TO-3P (Pb-Free)	30 Units/Rail

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case		0.83	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 30 \text{ mA}, I_B = 0$)	V _{CEO(sus)}	250	-	V
Collector Cutoff Current (V _{CB} = 250 V, I _E = 0)	Ісво	-	10	μΑ
Emitter Cutoff Current $(V_{EB} = 5.0 \text{ V, } I_{C} = 0)$	I _{EBO}	-	5.0	μΑ
ON CHARACTERISTICS				
DC Current Gain $ \begin{aligned} &(I_C = 0.5 \text{ A, V}_{CE} = 5.0 \text{ V}) \\ &(I_C = 1.0 \text{ A, V}_{CE} = 5.0 \text{ V}) \\ &(I_C = 3.0 \text{ A, V}_{CE} = 5.0 \text{ V}) \end{aligned} $	h _{FE}	75 75 75	150 150 150	-
Collector–Emitter Saturation Voltage (I _C = 5.0 A, I _B = 0.5 A)	V _{CE(sat)}	-	1.0	V
Base-Emitter On Voltage (I _C = 5.0 A, V _{CE} = 5.0 V)	V _{BE(on)}	-	1.2	V
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (I _C = 1.0 A, V _{CE} = 5.0 V, f _{test} = 1.0 MHz)	f⊤	30	-	MHz
Output Capacitance (V _{CB} = 10 V, I _E = 0, f _{test} = 1.0 MHz)	C _{ob}	-	400	pF

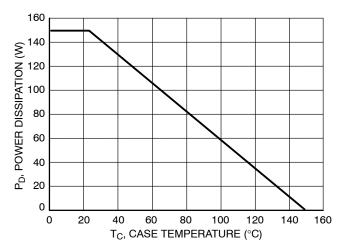


Figure 1. Power Derating

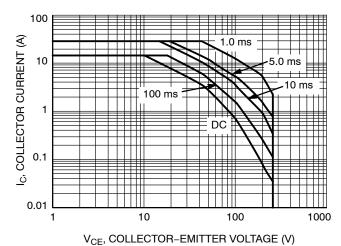


Figure 2. Safe Operating Area

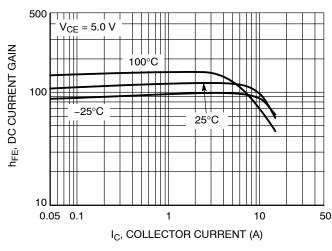


Figure 3. NJW0281G DC Current Gain

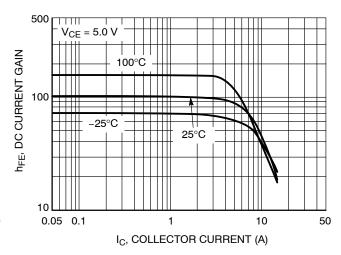


Figure 4. NJW0302G DC Current Gain

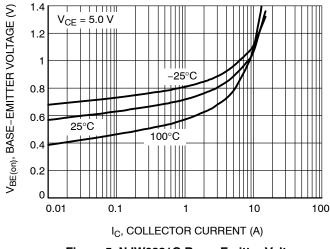


Figure 5. NJW0281G Base-Emitter Voltage

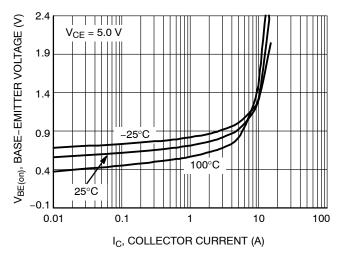


Figure 6. NJW0302G Base-Emitter Voltage

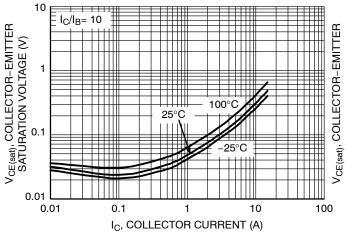


Figure 7. NJW0281G Saturation Voltage

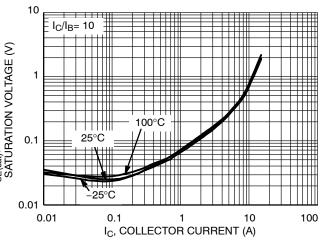


Figure 8. NJW0302G Saturation Voltage

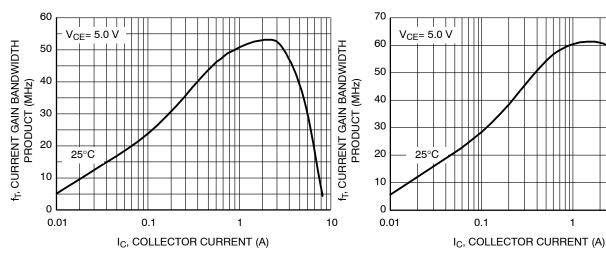


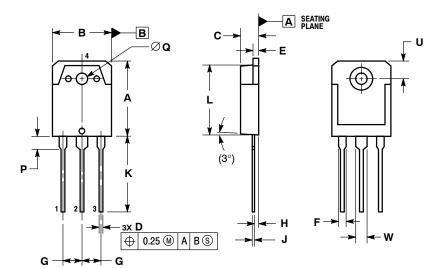
Figure 9. NJW0281G Current Gain Bandwidth Product

Figure 10. NJW0302G Current Gain Bandwidth Product

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PACKAGE DIMENSIONS

TO-3P-3LD CASE 340AB-01 **ISSUE A**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	19.70	19.90	20.10
В	15.40	15.60	15.80
С	4.60	4.80	5.00
D	0.80	1.00	1.20
E	1.45	1.50	1.65
F	1.80	2.00	2.20
G	5.45 BSC		
Н	1.20	1.40	1.60
J	0.55	0.60	0.75
K	19.80	20.00	20.20
L	18.50	18.70	18.90
P	3.30	3.50	3.70
Q	3.10	3.20	3.50
U	5.00 REF		
w	2.80	3.00	3.20

STYLE 1:

PIN 1. BASE 2 COLLECTOR

3. **EMITTER**

COLLECTOR

STYLE 2:

PIN 1. ANODE 2 CATHODE ANODE 3.

CATHODE

STYLE 3:

PIN 1. GATE DRAIN
 SOURCE DRAIN

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